

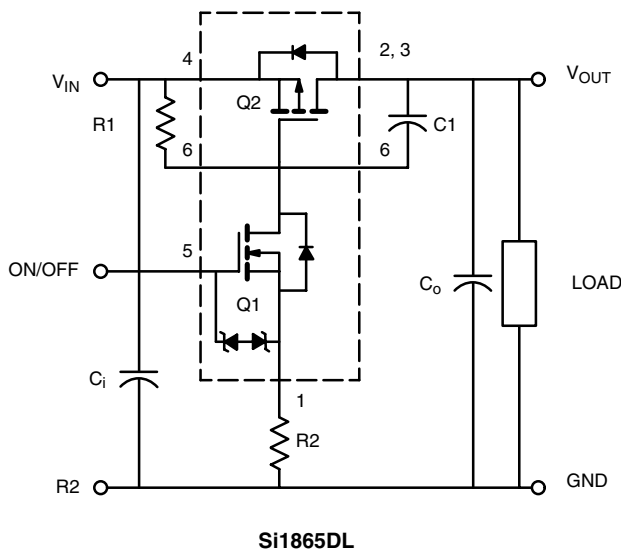
Load Switch with Level-Shift

| PRODUCT SUMMARY | | |
|----------------------|----------------------------------|--------------------|
| V _{DS2} (V) | R _{DS(on)} (Ω) | I _D (A) |
| 1.8 to 8 | 0.215 at V _{IN} = 4.5 V | ± 1.2 |
| | 0.300 at V _{IN} = 2.5 V | ± 1.0 |
| | 0.440 at V _{IN} = 1.8 V | ± 0.7 |

DESCRIPTION

The Si1865DL includes a p- and p-channel MOSFET in a single SC70-6 package. The low on-resistance p-channel TrenchFET is tailored for use as a load switch. The n-channel, with an external resistor, can be used as a level-shift to drive the p-channel load-switch. The n-channel MOSFET has internal ESD protection and can be driven by logic signals as low as 1.5 V. The Si1865DL operates on supply lines from 1.8 V to 8 V, and can drive loads up to 1.2 A.

APPLICATION CIRCUITS

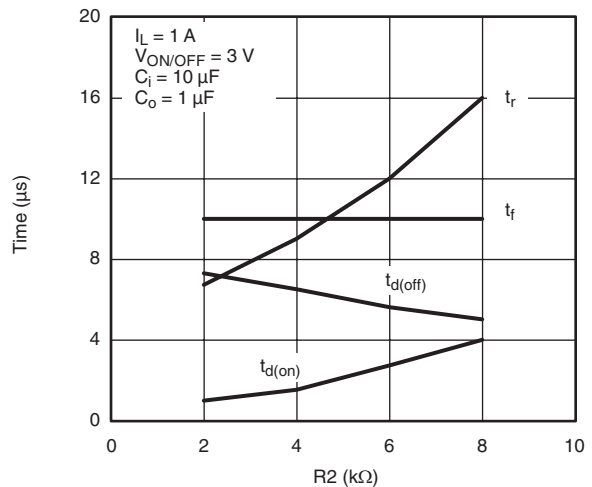


| COMPONENTS | | |
|------------|----------------------------|-------------------------|
| R1 | Pull-Up Resistor | Typical 10 kΩ to 1 mΩ* |
| R2 | Optional Slew-Rate Control | Typical 0 kΩ to 100 kΩ* |
| C1 | Optional Slew-Rate Control | Typical 1000 pF |

* Minimum R1 value should be least 10 x R2 to ensure Q1 turn-on.

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- 215 mΩ Low R_{DS(on)} TrenchFET[®]
- 1.8 V to 8 V Input
- 1.5 V to 8 V Logic Level Control
- Low Profile, Small Footprint SC70-6 Package
- 2000 V ESD Protection On Input Switch, V_{ON/OFF}
- Adjustable Slew-Rate
- 1.8 V Rated
- Compliant to RoHS Directive 2002/95/EC

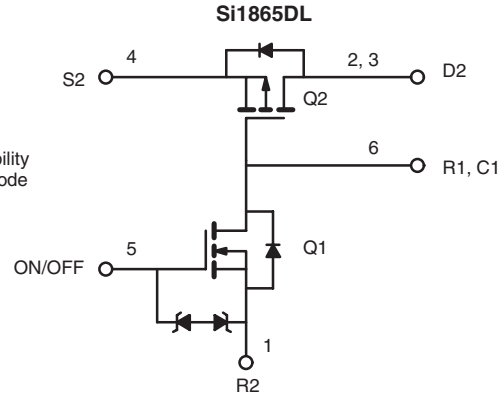
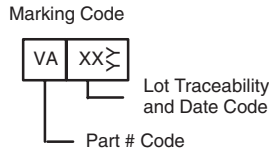
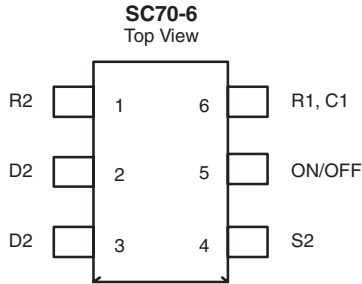


Note: For R2 switching variations with other V_{IN}/R1 combinations see Typical Characteristics

Switching Variation
R2 at V_{IN} = 2.5 V, R1 = 20 kΩ

The Si1865DL is ideally suited for high-side load switching in portable applications. The integrated n-channel level-shift devices saves space by reducing external components. The slew rate is set externally so that rise-times can be tailored to different load types.

FUNCTIONAL BLOCK DIAGRAM



Ordering Information: Si1865DL-T1-E3 (Lead (Pb)-free)
Si1865DL-T1-GE3 (Lead (Pb)-free and Halogen-free)

| ABSOLUTE MAXIMUM RATINGS $T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted | | | |
|--|----------------------------|-------------|------------------|
| Parameter | Symbol | Limit | Unit |
| Input Voltage | V_{IN} | 8 | V |
| ON/OFF Voltage | $V_{ON/OFF}$ | 8 | |
| Load Current | Continuous ^{a, b} | ± 1.2 | A |
| | Pulsed ^{b, c} | ± 3 | |
| Continuous Intrinsic Diode Conduction ^a | I_S | - 0.4 | |
| Maximum Power Dissipation ^a | P_D | 0.4 | W |
| Operating Junction and Storage Temperature Range | T_J, T_{stg} | - 55 to 150 | $^\circ\text{C}$ |
| ESD Rating, MIL-STD-883C Human Body Model (100 pF, 1500 Ω) | ESD | 2 | kV |

| THERMAL RESISTANCE RATINGS | | | | |
|---|------------|---------|---------|--------------------|
| Parameter | Symbol | Typical | Maximum | Unit |
| Maximum Junction-to-Ambient (continuous current) ^a | R_{thJA} | 260 | 320 | $^\circ\text{C/W}$ |
| Maximum Junction-to-Foot (Q2) | R_{thJC} | 180 | 220 | |

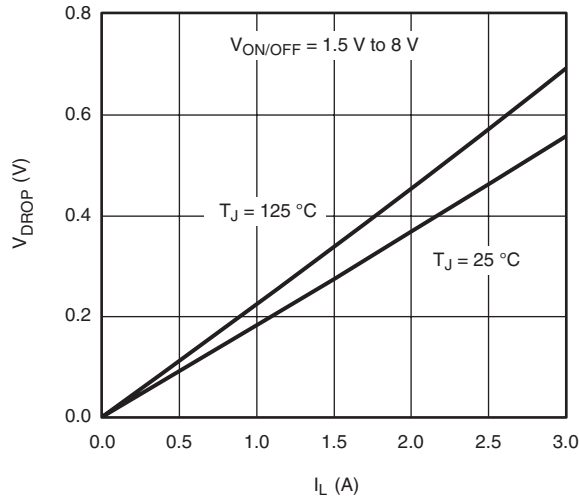
| SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted | | | | | | |
|--|--------------|--|------|-------|-------|---------------|
| Parameter | Symbol | Test Conditions | Min. | Typ. | Max. | Unit |
| OFF Characteristics | | | | | | |
| Reverse Leakage Current | V_{IN} | $V_{IN} = 8\text{ V}, V_{ON/OFF} = 0\text{ V}$ | | | 1 | μA |
| Diode Forward Voltage | I_Q | $I_S = - 0.4\text{ A}$ | | 0.85 | 1.1 | V |
| ON Characteristics | | | | | | |
| Input Voltage | V_{IN} | | 1.8 | | 8 | V |
| On-Resistance (P-Channel) at 1 A | $R_{DS(on)}$ | $V_{ON/OFF} = 1.5\text{ V}, V_{IN} = 4.5\text{ V}, I_D = 1.2\text{ A}$ | | 0.180 | 0.215 | Ω |
| | | $V_{ON/OFF} = 1.5\text{ V}, V_{IN} = 2.5\text{ V}, I_D = 1.0\text{ A}$ | | 0.250 | 0.300 | |
| | | $V_{ON/OFF} = 1.5\text{ V}, V_{IN} = 1.8\text{ V}, I_D = 0.7\text{ A}$ | | 0.367 | 0.440 | |
| On-State (P-Channel) Drain-Current | $I_{D(on)}$ | $V_{IN-OUT} \leq 0.2\text{ V}, V_{IN} = 5\text{ V}, V_{ON/OFF} = 1.5\text{ A}$ | 1 | | | A |
| | | $V_{IN-OUT} \leq 0.3\text{ V}, V_{IN} = 3\text{ V}, V_{ON/OFF} = 1.5\text{ A}$ | 1 | | | |

Notes:

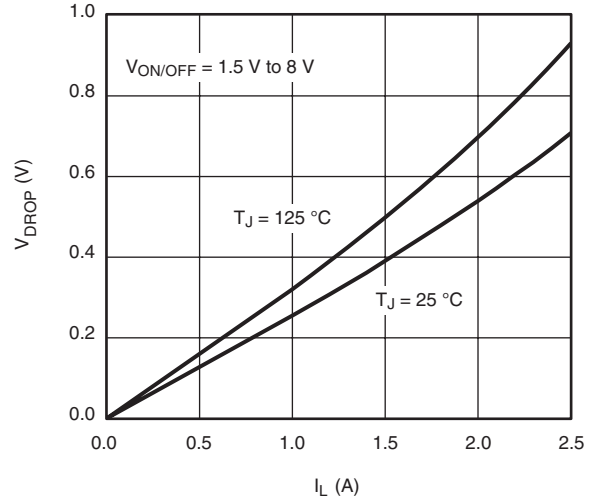
- a) Surface mounted on FR4 board.
- b) $V_{IN} = 8\text{ V}, V_{ON/OFF} = 8\text{ V}, T_A = 25\text{ }^\circ\text{C}$.
- c) Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

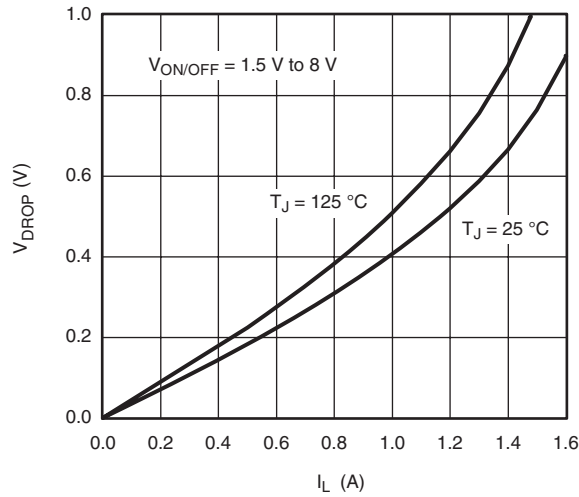
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



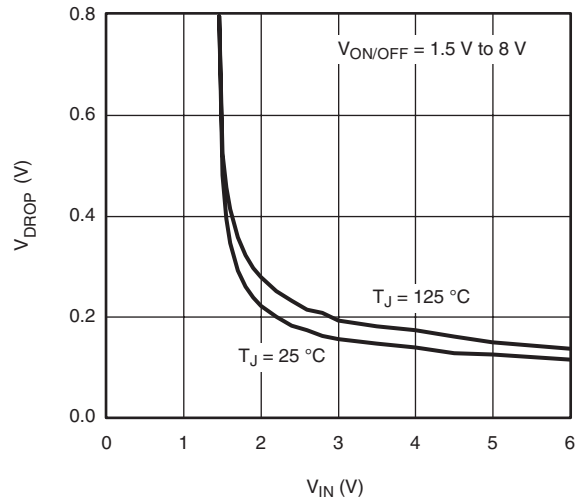
V_{DROP} vs. I_L at V_{IN} = 4.5 V



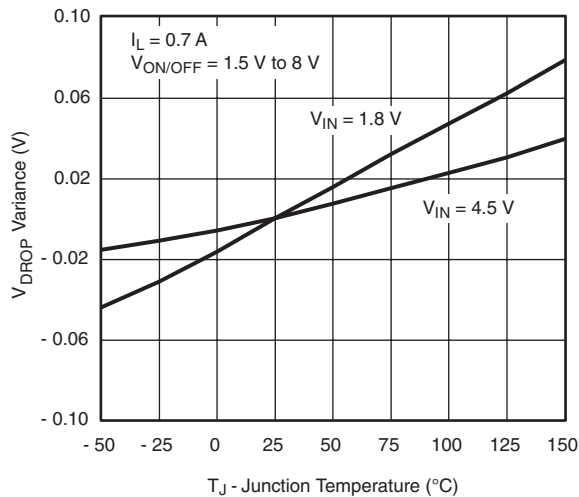
V_{DROP} vs. I_L at V_{IN} = 2.5 V



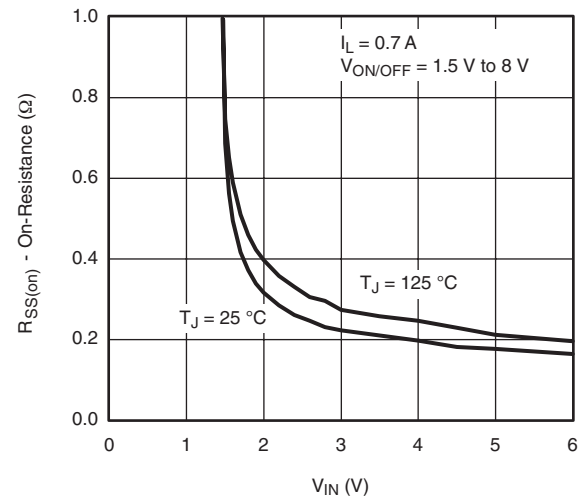
V_{DROP} vs. I_L at V_{IN} = 1.8 V



V_{DROP} vs. I_L at I_L = 0.7 A

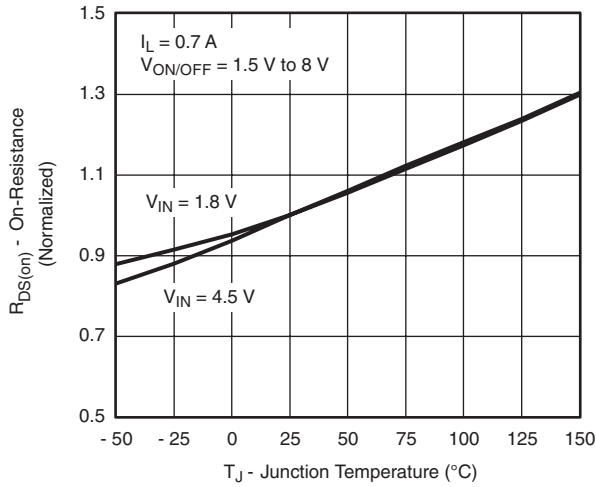


V_{DROP} Variance vs. Junction Temperature

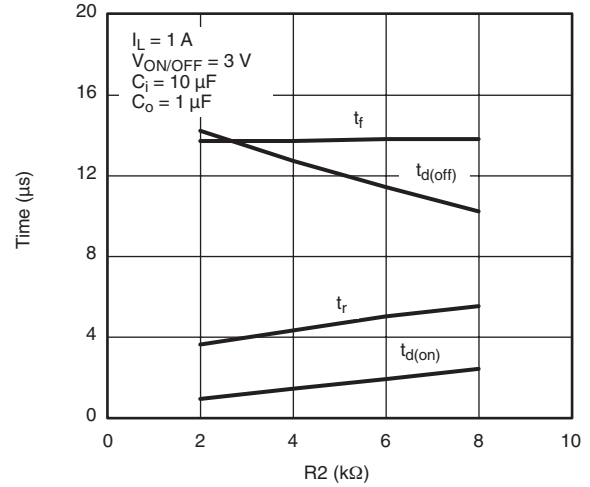


On-Resistance vs. Input Voltage

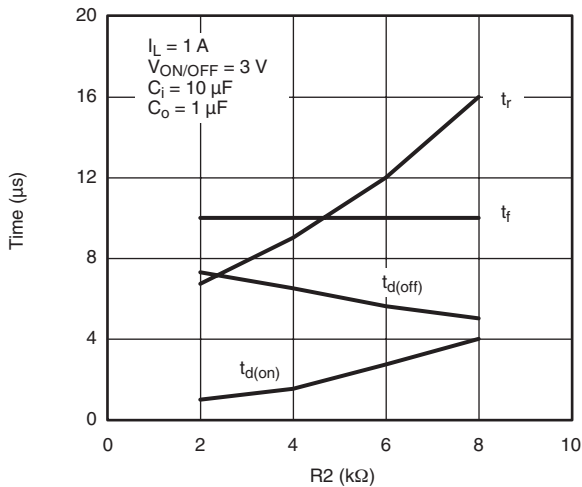
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



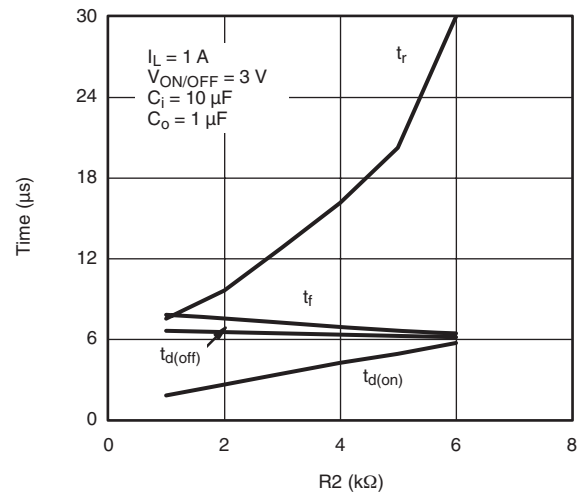
Normalized On-Resistance vs. Junction Temperature



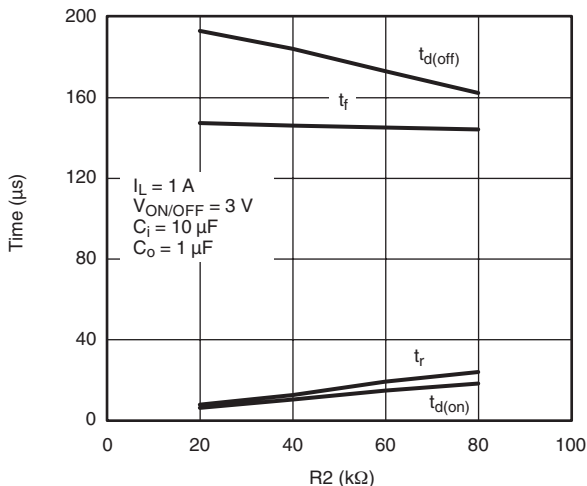
Switching Variation R2 at V_IN = 1.8 V, R1 = 20 kΩ



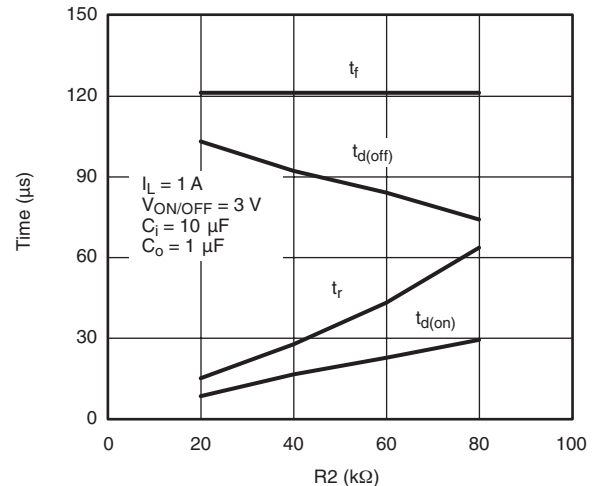
Switching Variation R2 at V_IN = 2.5 V, R1 = 20 kΩ



Switching Variation R2 at V_IN = 1.8 V, R1 = 20 kΩ

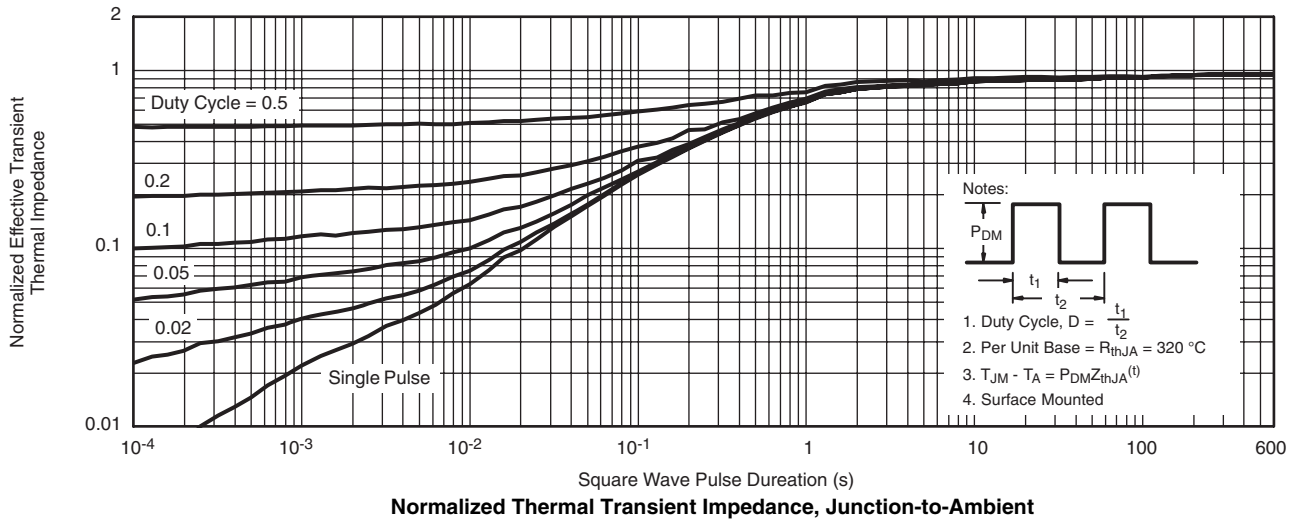
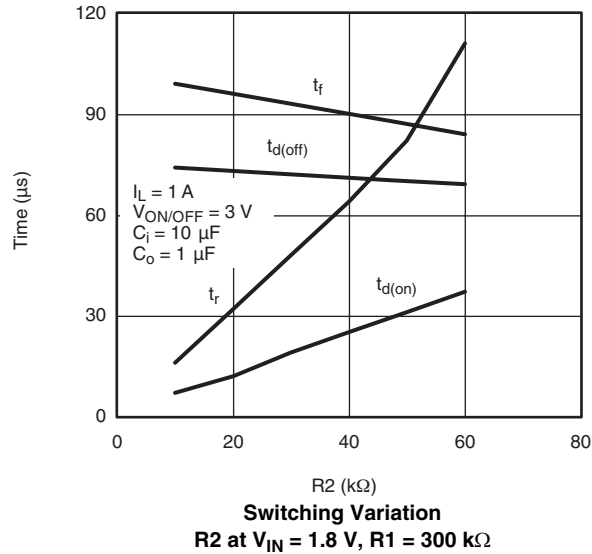


Switching Variation R2 at V_IN = 4.5 V, R1 = 300 kΩ



Switching Variation R2 at V_IN = 2.5 V, R1 = 300 kΩ

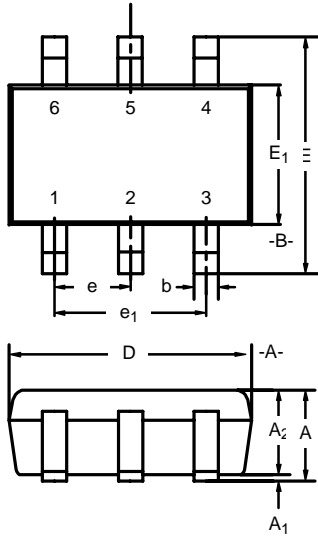
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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SC-70: 6-LEADS



| Dim | MILLIMETERS | | | INCHES | | |
|----------------|-------------|------|------|----------|-------|-------|
| | Min | Nom | Max | Min | Nom | Max |
| A | 0.90 | - | 1.10 | 0.035 | - | 0.043 |
| A ₁ | - | - | 0.10 | - | - | 0.004 |
| A ₂ | 0.80 | - | 1.00 | 0.031 | - | 0.039 |
| b | 0.15 | - | 0.30 | 0.006 | - | 0.012 |
| c | 0.10 | - | 0.25 | 0.004 | - | 0.010 |
| D | 1.80 | 2.00 | 2.20 | 0.071 | 0.079 | 0.087 |
| E | 1.80 | 2.10 | 2.40 | 0.071 | 0.083 | 0.094 |
| E ₁ | 1.15 | 1.25 | 1.35 | 0.045 | 0.049 | 0.053 |
| e | 0.65BSC | | | 0.026BSC | | |
| e ₁ | 1.20 | 1.30 | 1.40 | 0.047 | 0.051 | 0.055 |
| L | 0.10 | 0.20 | 0.30 | 0.004 | 0.008 | 0.012 |
| α | 7°Nom | | | 7°Nom | | |

ECN: S-03946—Rev. B, 09-Jul-01
DWG: 5550

Dual-Channel LITTLE FOOT® SC-70 6-Pin MOSFET Recommended Pad Pattern and Thermal Performance

INTRODUCTION

This technical note discusses the pin-outs, package outlines, pad patterns, evaluation board layout, and thermal performance for dual-channel LITTLE FOOT power MOSFETs in the SC-70 package. These new Vishay Siliconix devices are intended for small-signal applications where a miniaturized package is needed and low levels of current (around 250 mA) need to be switched, either directly or by using a level shift configuration. Vishay provides these devices with a range of on-resistance specifications in 6-pin versions. The new 6-pin SC-70 package enables improved on-resistance values and enhanced thermal performance.

PIN-OUT

Figure 1 shows the pin-out description and Pin 1 identification for the dual-channel SC-70 device in the 6-pin configuration.

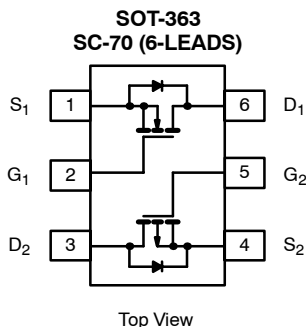


FIGURE 1.

For package dimensions see outline drawing SC-70 (6-Leads) (<http://www.vishay.com/doc?71154>)

BASIC PAD PATTERNS

See Application Note 826, *Recommended Minimum Pad Patterns With Outline Drawing Access for Vishay Siliconix MOSFETs*, (<http://www.vishay.com/doc?72286>) for the 6-pin SC-70. This basic pad pattern is sufficient for the low-power

applications for which this package is intended. For the 6-pin device, increasing the pad patterns yields a reduction in thermal resistance on the order of 20% when using a 1-inch square with full copper on both sides of the printed circuit board (PCB).

EVALUATION BOARDS FOR THE DUAL SC70-6

The 6-pin SC-70 evaluation board (EVB) measures 0.6 inches by 0.5 inches. The copper pad traces are the same as described in the previous section, *Basic Pad Patterns*. The board allows interrogation from the outer pins to 6-pin DIP connections permitting test sockets to be used in evaluation testing.

The thermal performance of the dual SC-70 has been measured on the EVB with the results shown below. The minimum recommended footprint on the evaluation board was compared with the industry standard 1-inch square FR4 PCB with copper on both sides of the board.

THERMAL PERFORMANCE

Junction-to-Foot Thermal Resistance (the Package Performance)

Thermal performance for the dual SC-70 6-pin package measured as junction-to-foot thermal resistance is 300°C/W typical, 350°C/W maximum. The “foot” is the drain lead of the device as it connects with the body. Note that these numbers are somewhat higher than other LITTLE FOOT devices due to the limited thermal performance of the Alloy 42 lead-frame compared with a standard copper lead-frame.

Junction-to-Ambient Thermal Resistance (dependent on PCB size)

The typical $R\theta_{JA}$ for the dual 6-pin SC-70 is 400°C/W steady state. Maximum ratings are 460°C/W for the dual. All figures based on the 1-inch square FR4 test board. The following example shows how the thermal resistance impacts power dissipation for the dual 6-pin SC-70 package at two different ambient temperatures.

| SC-70 (6-PIN) | |
|---|---|
| Room Ambient 25 °C | Elevated Ambient 60 °C |
| $P_D = \frac{T_{J(max)} - T_A}{R\theta_{JA}}$ | $P_D = \frac{T_{J(max)} - T_A}{R\theta_{JA}}$ |
| $P_D = \frac{150^{\circ}C - 25^{\circ}C}{400^{\circ}C/W}$ | $P_D = \frac{150^{\circ}C - 60^{\circ}C}{400^{\circ}C/W}$ |
| $P_D = 312 \text{ mW}$ | $P_D = 225 \text{ mW}$ |

NOTE: Although they are intended for low-power applications, devices in the 6-pin SC-70 will handle power dissipation in excess of 0.2 W.

Testing

To aid comparison further, Figure 2 illustrates the dual-channel SC-70 thermal performance on two different board sizes and two different pad patterns. The results display the thermal performance out to steady state. The measured steady state values of $R\theta_{JA}$ for the dual 6-pin SC-70 are as follows:

| LITTLE FOOT SC-70 (6-PIN) | |
|--|----------|
| 1) Minimum recommended pad pattern (see Figure 2) on the EVB of 0.5 inches x 0.6 inches. | 518 °C/W |
| 2) Industry standard 1" square PCB with maximum copper both sides. | 413 °C/W |

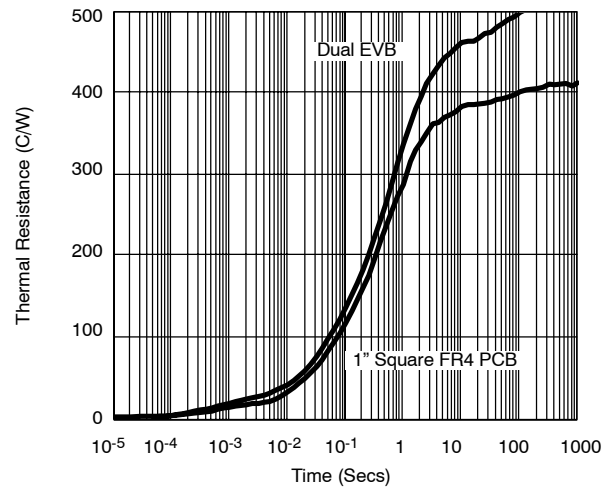


FIGURE 2. Comparison of Dual SC70-6 on EVB and 1" Square FR4 PCB.

The results show that if the board area can be increased and maximum copper traces are added, the thermal resistance reduction is limited to 20%. This fact confirms that the power dissipation is restricted with the package size and the Alloy 42 leadframe.

ASSOCIATED DOCUMENT

Single-Channel LITTLE FOOT SC-70 6-Pin MOSFET Copper Leadframe Version, REcommended Pad Pattern and Thermal Performance, AN815, (<http://www.vishay.com/doc?71334>).

RECOMMENDED MINIMUM PADS FOR SC-70: 6-Lead



Recommended Minimum Pads
Dimensions in Inches/(mm)

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